

AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph beginning at Page 9, line 24, with the following rewritten paragraph:

--After forming the pure Ge or SiGe layer (or optional cap layer) atop the initial structure, the structure shown in either FIG 1B, 2B, 3A or 3B is then heated, i.e., annealed, at a temperature which permits interdiffusion of Ge throughout first single crystal Si layer 14, SiGe or pure Ge layer 16 and, if present, the optional Si cap thereby forming substantially relaxed, single crystal SiGe layer 20 atop said barrier layer. The resultant structure that is formed after the heating step is performed is shown, for example, in FIG. 1C or 2C. Note that oxide layer 22 is formed atop layer 20 during the heating step. This oxide layer is typically, but not always, removed from the structure after the heating step using a conventional wet etch process wherein a chemical etchant such as HF that has a high selectivity for removing oxide as compared to SiGe is employed.--